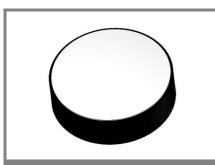
AG 3A ... AG 3M



Silicon Rectifier Cells

with polysiloxan passivation

AG 3A ... AG3M Forward Current: 3 A Reverse Voltage: 50 to 1000 V Publish Data

Features

Mechanical Data

• Weight approx. 0.3g

• ²⁾ I_F = 3A, Tj = 25°C

Туре	Repetitive peak reverse voltage V _{RRM}	Surge peak reverse voltage V _{RSM}	Max. reverse recovery time $I_F = A$ $I_R = A$ $I_{RR} = A$ t_{rr}	Max. forward voltage
	V	V	ns	V _F ²⁾
AG 3A	50	80	/	<1,2
AG 3B	100	130	/	<1,2
AG 3D	200	250	/	<1,2
AG 3G	400	450	/	<1,2
AG 3J	600	700	/	<1,2
AG 3K	800	1000	/	<1,2
AG 3M	1000	1300	/	<1,2

Absolute Maximum Ratings $T_c = 25^{\circ}C$ unless otherwise specified					
Symbol	Conditions	Values	Units		
I _{FAV}	Max. averaged fwd. current, R-load, $T_A = 100 \ ^\circ C^{-1)}$	3	А		
I _{FRM}	Repetitive peak forward current f > 15 Hz ¹⁾	30	А		
I _{FSM}	Peak forward surge current 50 Hz half sinus-wave ³⁾	150	А		
i²t	Rating for fusing, t < 10 ms $^{3)}$	110	A²s		
R _{thA}	Max. thermal resistance junction to ambient ¹⁾		K/W		
R _{thT}	Max. thermal resistance junction to terminals ¹⁾		K/W		
T _j	Operating junction temperature	-50 +150°C	°C		
Τ _s	Storage temperature	-50 +150°C	°C		

Characte	aracteristics T _c = 25°C unless otherwise speci		ecified
Symbol	Conditions	Values	Units
I _R	Maximum leakage current, T_j = 25 °C; V_R = V_{RRM}	10	μA
	$T_j = 100 \text{ °C}; V_R = V_{RRM}$	1	mA
C ¹	Typical junction capacitance (at MHz and applied reverse voltage of V)		pF
Q _{rr}	Reverse recovery charge ($U_R = V$; $I_F = A$; $dI_F/dt = A/ms$)		μC
E _{RSM}	Non repetitive peak reverse avalanche energy ($I_R = mA; T_j = °C;$ inductive load switched off)		mJ

